

SNJ450113 (TO-18) (Preliminary)**N-Channel Silicon Junction Field-Effect Transistor**

- Low R(on) Switch
- Low-Noise, High Gain Amplifier

Absolute maximum ratings at T_A = 25°C

Reverse Gate Source & Gate Drain Voltage -25V
 Continuous Forward Gate Current 10 mA
 Operating Temperature Range -55°C to +150°C
 Storage Temperature Range -65°C to +175°C

At 25°C free air temperature

Static Electrical Characteristics		Process NJ450				
		Min	Typ	Max	Unit	Test Conditions
Gate Source Breakdown Voltage	V _{(BR)GSS}	-40	-45		V	I _G = -1 uA, V _{DS} = 0 V
Gate Reverse Current	I _{GSS}		-50	-1000	pA	V _{GS} = -10 V, V _{DS} = 0 V
Gate Source Cutoff Voltage	V _{GS(OFF)}	-0.3			V	V _{DS} = 10 V, I _D = 1 nA
Drain Saturation Current (pulsed)	I _{DSS}	8		20	mA	V _{DS} = 15 V, V _{GS} = 0 V
Dynamic Electrical Characteristics						
Forward Transconductance	g _{fs}		20	30	mS	V _{DS} = 15 V, V _{GS} = 0 V f = 1 kHz
Common-Source Input Capacitance	C _{iss}			75	pF	V _{DS} = 0V, V _{GS} = -10 V f = 1 MHz
Feedback Capacitance	C _{iss}		15		pF	V _{DS} = 0V, V _{GS} = -10 V f = 1 MHz

TO-18 Package

Dimensions in inches (mm)

